

ABSTRACT OF THE DISCLOSURE

At the time of plasma igniting or during plasma processing, only optimizing the distance between electrodes in each case caused a limitation to the prevention of charging damage. To resolve this, a novel plasma processing method employs a plasma processing apparatus which includes an upper electrode to which first high-frequency power is applied, a lower electrode to which second high-frequency power is applied, and a lift mechanism for controlling the spacing between the upper and lower electrodes. The first high-frequency power is applied to the upper electrode to cause plasma igniting. The method is adapted to make the spacing between the upper and lower electrodes larger at least at the time of plasma extinction than during plasma processing of a wafer on the lower electrode.